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8. (once amended) A process according to claim [I further comprising] 1 wherein cleaning the n-type converted copper indium diselenide film surface comprises rinsing with deionized water and etching with dilute hydrochloric acid.

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10. (once amended) A thin film photovoltaic device comprising, in order, a first layer of p-type copper indium diselenide semiconductor having a type converted upper region rendered n-type by thermal diffusion of a group IIb halide and [(a,b) and VII elemental salt], a second layer of high resistivity zinc oxide semiconductor in contact with said first layer, and a third layer of low resistivity zinc oxide semiconductor in contact with said second layer.

11. (once amended) A device according to claim 10, wherein the group IIb halide [(a,b) and VII elemental salt] is zinc chloride.

In the Abstract:

Page 10, line 6, after "group II", delete "(a,b)" and substitute therefor --b--.

Page 10, line 7, after "and a", delete "group VII element" and substitute therefor --halide--

REMARKS

The objections to the drawings are noted. Formal drawings will be submitted at such time as this application is in condition for allowance. Claim 1 stands rejected under 35 USC 112, first paragraph, as not supported by the disclosure. Claim 1 has been amended to a scope commensurate with the support of the specification. The basis for addition appears on page 6, line 8 to 9. Enablement of the group IIb halides is supported in the disclosure of zinc chloride "as the doping source" because it is highly predictable by one of ordinary skill in the art of

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